

isc Silicon PNP Power Transistor

2SA1006A

DESCRIPTION

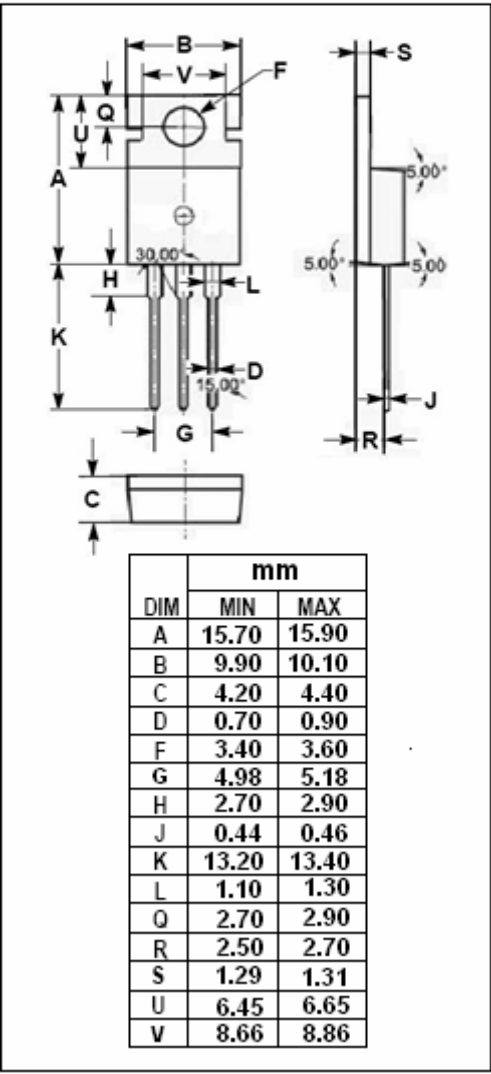
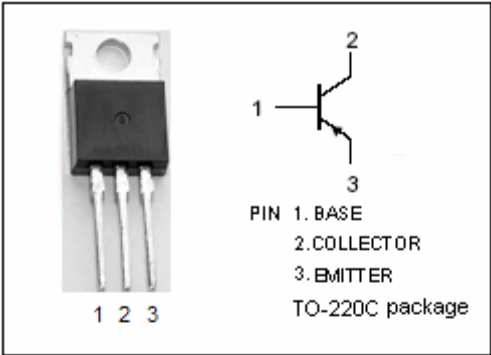
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -200V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SC2336A

APPLICATIONS

- Aaudio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation@ $T_a=25^\circ\text{C}$	1.5	W
	Total Power Dissipation@ $T_c=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SA1006A****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3.0V; I _C =0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -5mA ; V _{CE} = -5V	30			
h _{FE-2}	DC Current Gain	I _C = -150mA ; V _{CE} = -5V	60		320	
f _T	Current-Gain—Bandwidth Product	I _C = -100mA ; V _{CE} = -10V		80		MHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = -10V; f= 1.0MHz		45		pF

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320